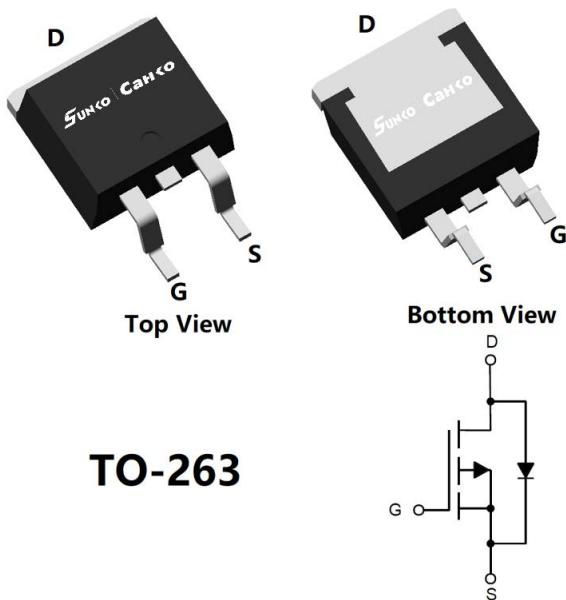


N-Channel Enhancement Mode Field Effect Transistor



Product Summary

- V_{DS} 100V
- I_D 70A
- $R_{DS(on)}$ (at $V_{GS}=10V$) <8.6 mohm
- $R_{DS(on)}$ (at $V_{GS}=4.5V$) <11 mohm
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	100	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	70	A
		44.2	
Pulsed Drain Current ^A	I_{DM}	280	A
Avalanche energy ^B	E_{AS}	200	mJ
Total Power Dissipation ^C	P_D	125	W
		50	
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	°C

■ Thermal resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	$R_{\theta JA}$	12	15	°C/W
Thermal Resistance Junction-to-Ambient ^D		50	60	
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.8	1.0	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
SCB70G10A	F2	SCB70G10A	800	/	8000	13" reel

■ Electrical Characteristics ($T_j=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=100, V_{\text{GS}}=0\text{V}$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}= \pm 20\text{V}, V_{\text{DS}}=0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1	1.8	3	V
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}= 10\text{V}, I_{\text{D}}=20\text{A}$		7.2	8.6	$\text{m}\Omega$
		$V_{\text{GS}}= 4.5\text{V}, I_{\text{D}}=20\text{A}$		8.8	11	$\text{m}\Omega$
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=20\text{A}, V_{\text{GS}}=0\text{V}$			1.3	V
Maximum Body-Diode Continuous Current	I_{S}				70	A
Gate resistance	R_{G}	f= 1 MHz, Open drain		0.68		Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{DS}}=50\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		2270		pF
Output Capacitance	C_{oss}			797		
Reverse Transfer Capacitance	C_{rss}			36		
Switching Parameters						
Total Gate Charge	Q_{g}	$V_{\text{GS}}=10\text{V}, V_{\text{DS}}=50\text{V}, I_{\text{D}}=25\text{A}$		32		nC
Gate-Source Charge	Q_{gs}			11.1		
Gate-Drain Charge	Q_{gd}			4.78		
Reverse Recovery Chrage	Q_{rr}	$I_{\text{F}}=20\text{A}, dI/dt=100\text{A/us}$		84		ns
Reverse Recovery Time	t_{rr}			51.5		
Turn-on Delay Time	$t_{\text{D(on)}}$			51		
Turn-on Rise Time	t_{r}	$V_{\text{GS}}=10\text{V}, V_{\text{DD}}=50\text{V}, I_{\text{D}}=25\text{A}$ $R_{\text{GEN}}=2.2\Omega$		14.4		ns
Turn-off Delay Time	$t_{\text{D(off)}}$			69.2		
Turn-off fall Time	t_{f}			20.6		

- A. Repetitive rating; pulse width limited by max. junction temperature.
 B. $V_{\text{DD}}=50\text{V}$, $R_{\text{G}}=25\Omega$, $L=0.5\text{mH}$, $I_{\text{AS}}=25\text{A}$.
 C. P_{d} is based on max. junction temperature, using junction-case thermal resistance.
 D. The value of $R_{\theta\text{JA}}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta\text{JA}} \leq 10\text{s}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.

■ Typical Performance Characteristics

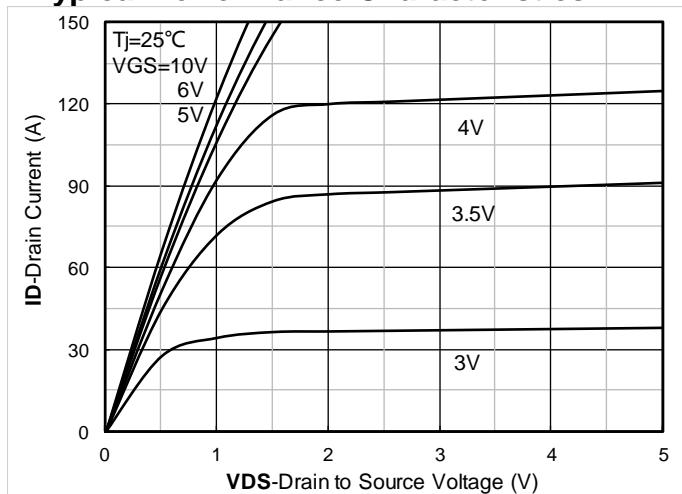


Figure1. Output Characteristics

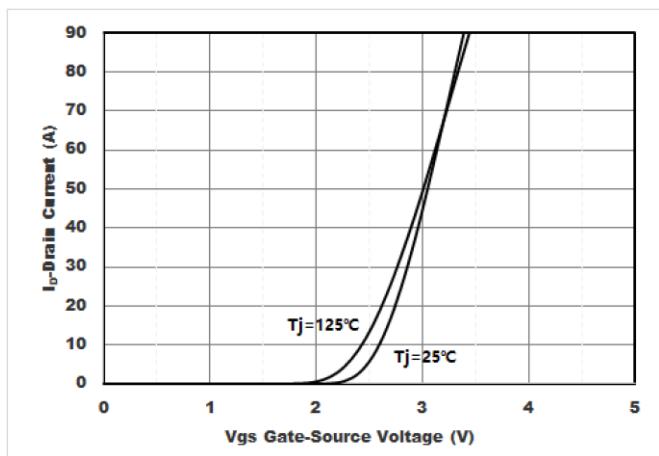


Figure2. Transfer Characteristics

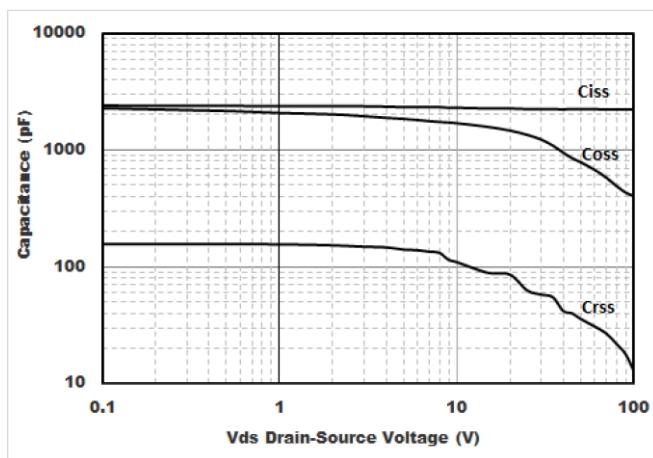


Figure3. Capacitance Characteristics

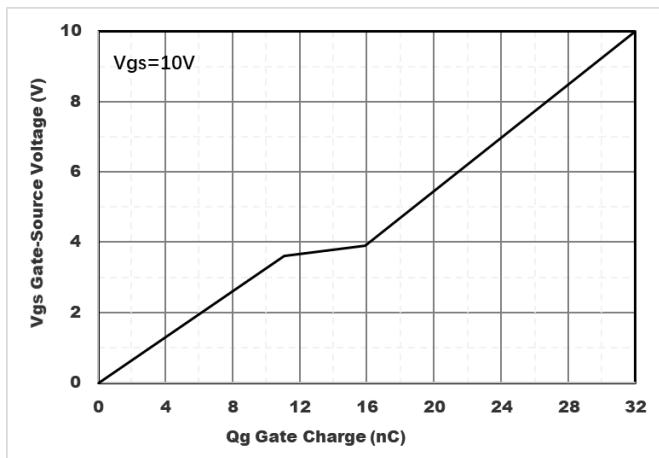


Figure4. Gate Charge

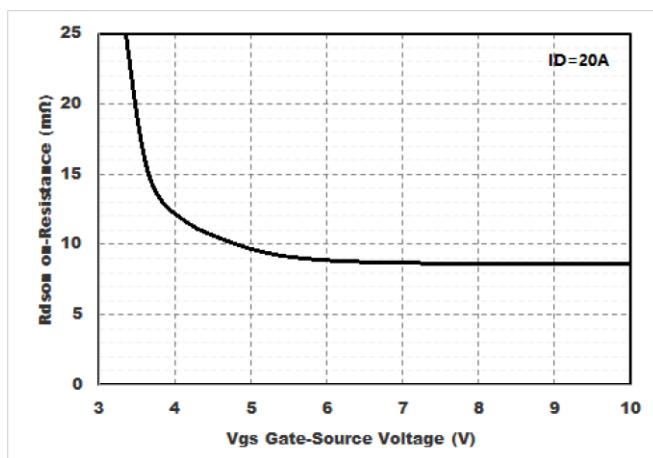


Figure5. : On-Resistance vs. Drain Current and Gate Voltage

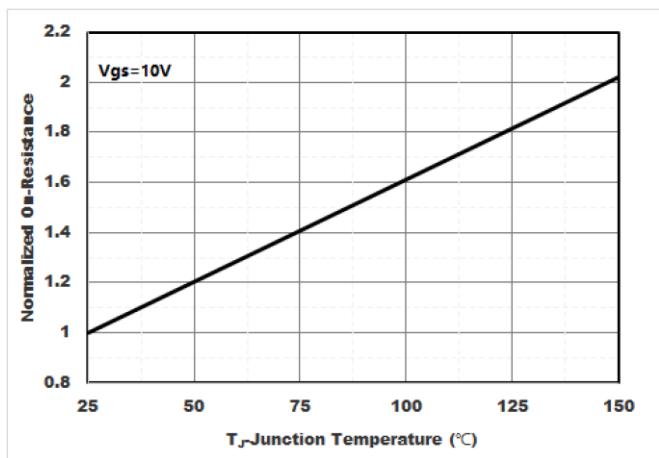


Figure6.Normalized On-Resistance

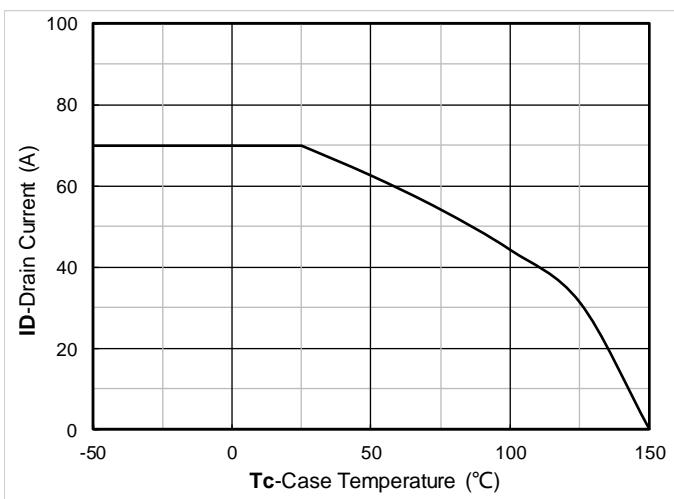


Figure 7. Drain current

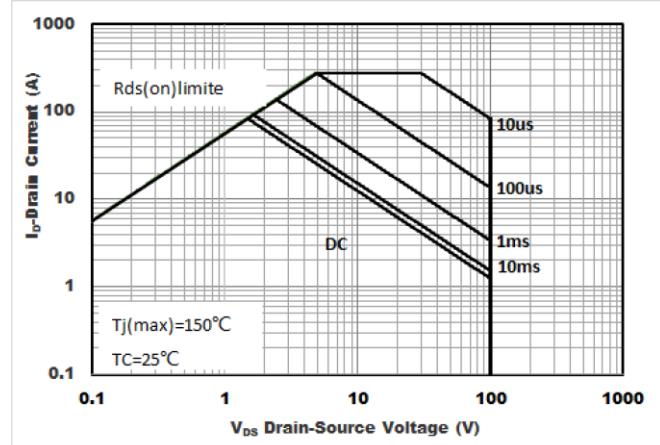


Figure 8. Safe Operation Area

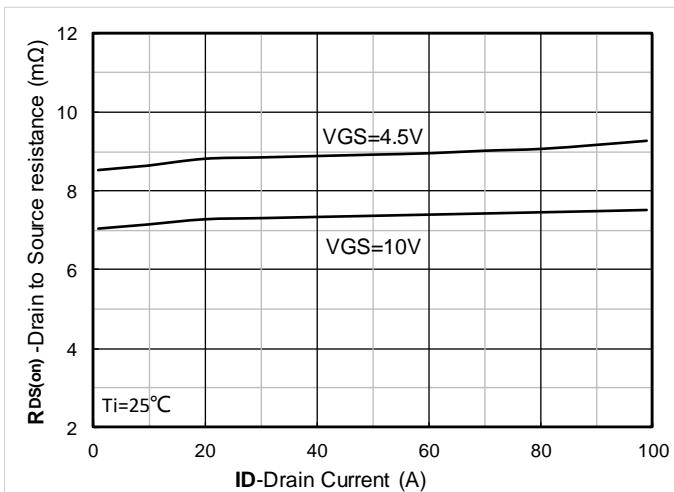
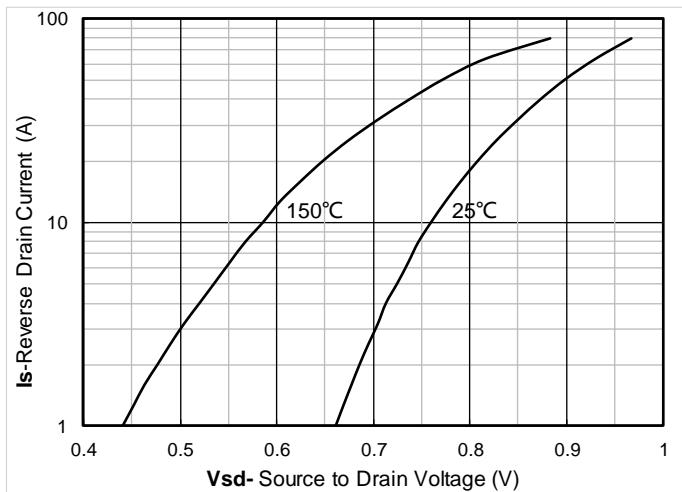
Figure 9. $R_{DS(on)}$ VS Drain Current

Figure 10. Forward characteristics of reverse diode

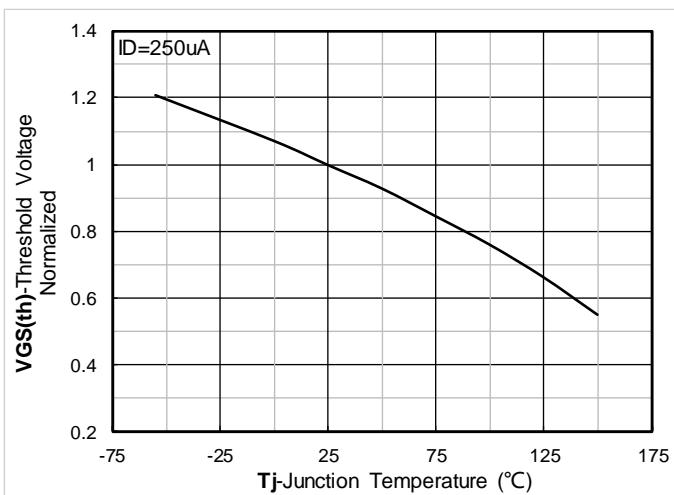


Figure 11. Normalized Threshold voltage

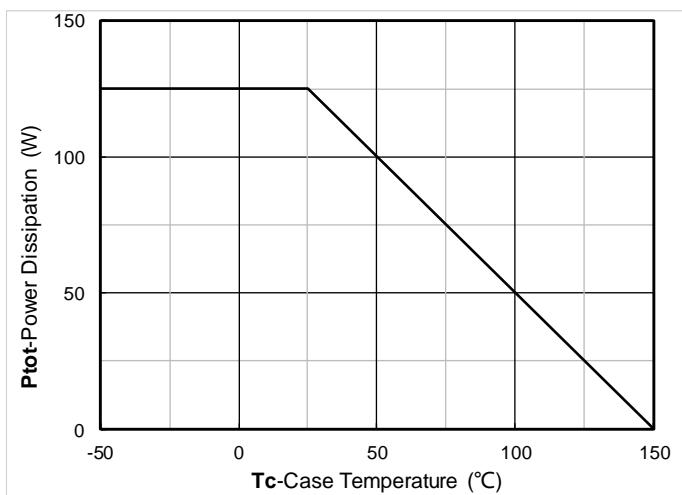


Figure 12. Power dissipation

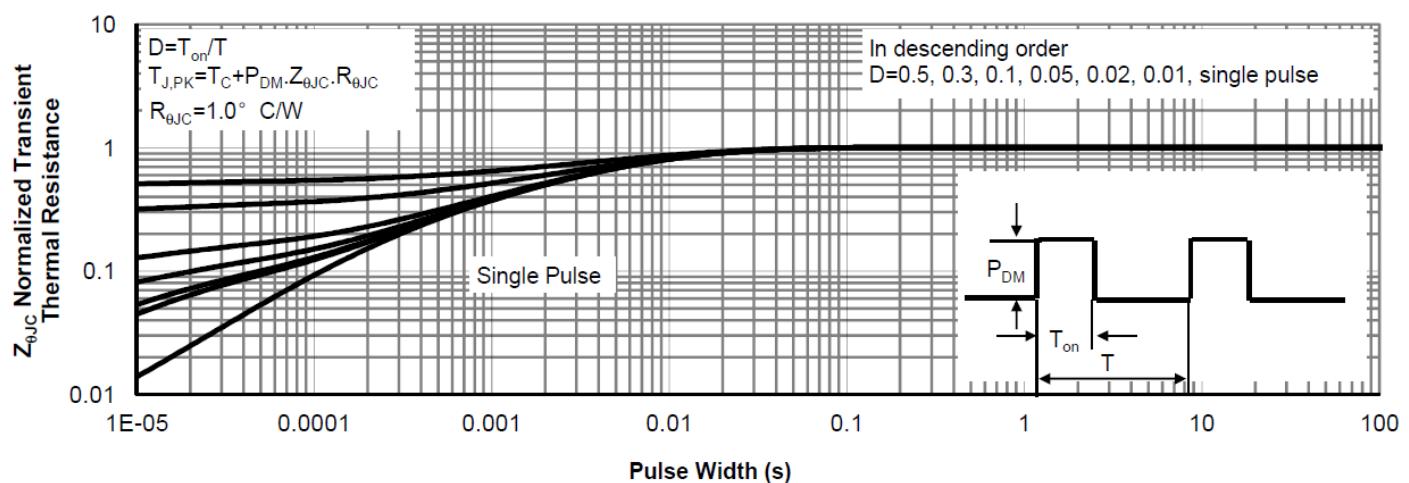
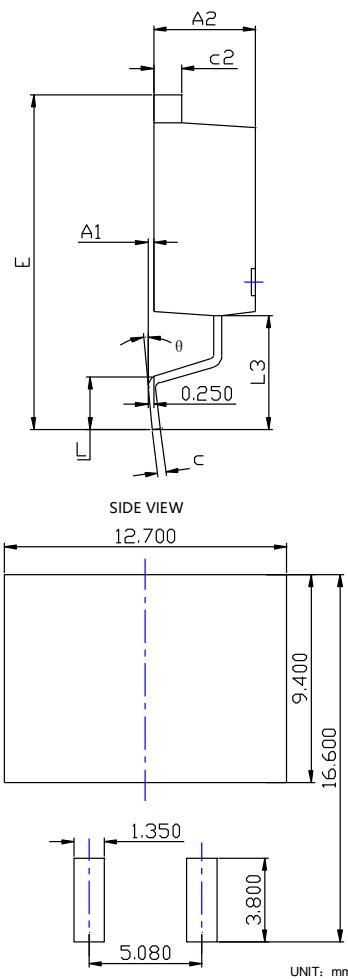
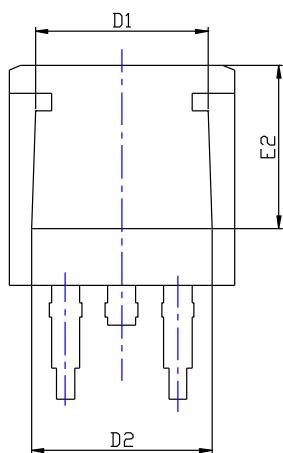
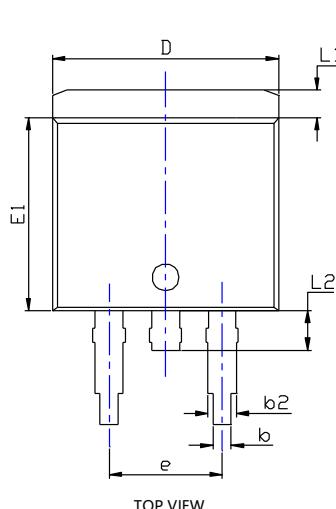


Figure13.Normalized Maximum Transient thermal impedance

■ TO-263-HY Package information



SYMBOL	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.010	0.000	---	0.250
A2	0.174	0.180	0.186	4.430	4.580	4.730
b	0.028	0.032	0.036	0.720	0.820	0.920
b2	0.046	0.050	0.054	1.180	1.280	1.380
c	0.013	0.015	0.018	0.330	0.390	0.450
c2	0.048	0.050	0.053	1.220	1.280	1.340
D	0.394	0.400	0.406	10.000	10.150	10.300
D1	0.295	0.307	0.319	7.500	7.800	8.100
D2	0.303	0.315	0.327	7.700	8.000	8.300
E	0.571	0.591	0.610	14.500	15.000	15.500
E1	0.337	0.341	0.348	8.550	8.700	8.850
E2	0.276	0.287	0.299	7.000	7.300	7.600
e	0.200BSC			5.080BSC		
L	0.070	---	0.110	1.790	---	2.790
L1	0.044	---	0.056	1.120	---	1.420
L2	0.030	---	0.070	0.770	---	1.770
L3	0.197REF			5.000REF		
θ	0°	---	8°	0°	---	8°

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

SUGGESTED SOLDER PAD LAYOUT

Disclaimer

The information presented in this document is for reference only. Russiansunc Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Russiansunc or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.russiansunco.com>, or consult your nearest Russiansunc's sales office for further assistance.